

## Power MOSFET

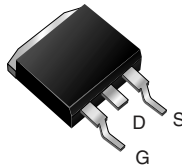
PRODUCT SUMMARY		
$V_{DS}$ (V)	200	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.30
$Q_g$ (Max.) (nC)	43	
$Q_{gs}$ (nC)	7.0	
$Q_{gd}$ (nC)	23	
Configuration	Single	

### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



D<sup>2</sup>PAK (TO-263)



N-Channel MOSFET

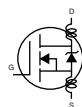
ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	200	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current	$V_{GS}$ at 10 V	$I_D$	$T_C = 25\text{ }^\circ\text{C}$	A
			$T_C = 100\text{ }^\circ\text{C}$	
Pulsed Drain Current <sup>a</sup>		$I_{DM}$	36	
Linear Derating Factor			0.59	W/ $^\circ\text{C}$
Linear Derating Factor (PCB Mount) <sup>e</sup>			0.025	
Single Pulse Avalanche Energy <sup>b</sup>		$E_{AS}$	250	mJ
Repetitive Avalanche Current <sup>a</sup>		$I_{AR}$	9.0	A
Repetitive Avalanche Energy <sup>a</sup>		$E_{AR}$	7.4	mJ
Maximum Power Dissipation		$P_D$	$T_C = 25\text{ }^\circ\text{C}$	W
Maximum Power Dissipation (PCB Mount) <sup>e</sup>			$T_A = 25\text{ }^\circ\text{C}$	
* Pb containing terminations are not RoHS compliant, exemptions may apply				
Peak Diode Recovery dV/dt <sup>c</sup>		dV/dt	5.0	V/ns


ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s	300 <sup>d</sup>	

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. V<sub>DD</sub> = 50 V, starting T<sub>J</sub> = 25 °C, L = 4.6 mH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 9.0 A (see fig. 12).
- c. I<sub>SD</sub> ≤ 9.0 A, di/dt ≤ 120 A/μs, V<sub>DD</sub> ≤ V<sub>DS</sub>, T<sub>J</sub> ≤ 150 °C.
- d. 1.6 mm from case.
- e. When mounted on 1" square PCB (FR-4 or G-10 material).

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	-	-	40	°C/W
Maximum Junction-to-Ambient	R <sub>thJA</sub>	-	-	62	
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	-	-	1.7	

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA		200	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA		-	0.24	-	V/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V		-	-	25	μA
		V <sub>DS</sub> = 160V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	250	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5.4 A <sup>b</sup>	-	0.30	-	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 5.4 A <sup>b</sup>		3.8	-	-	S
<b>Dynamic</b>							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1.0 MHz, see fig. 5		-	800	-	pF
Output Capacitance	C <sub>oss</sub>			-	240	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	76	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5.9 A, V <sub>DS</sub> = 160 V see fig. 6 and 13 <sup>b</sup>	-	-	43	nC
Gate-Source Charge	Q <sub>gs</sub>			-	-	7.0	
Gate-Drain Charge	Q <sub>gd</sub>			-	-	23	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, I <sub>D</sub> = 5.9 A R <sub>g</sub> = 12 Ω, R <sub>D</sub> = 16 Ω see fig. 10 <sup>b</sup>		-	9.4	-	ns
Rise Time	t <sub>r</sub>			-	28	-	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	39	-	
Fall Time	t <sub>f</sub>			-	20	-	
Internal Drain Inductance	L <sub>D</sub>	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	L <sub>S</sub>			-	7.5	-	

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	9.0	A
Pulsed Diode Forward Current <sup>a</sup>	I <sub>SM</sub>		-	-	36	
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 9.0 A, V <sub>GS</sub> = 0 V <sup>b</sup>	-	-	2.0	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = 5.9 A, di/dt = 100 A/μs <sup>b</sup>	-	170	340	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	1.1	2.2	μC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )				

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %.
- c. When mounted on 1" square PCB (FR-4 or G-10 material).

**TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**

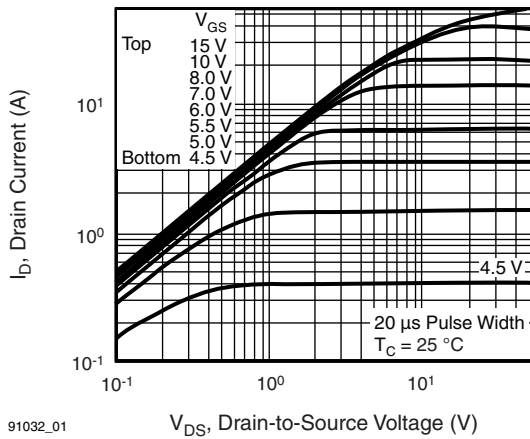


Fig. 1 - Typical Output Characteristics, T<sub>C</sub> = 25 °C

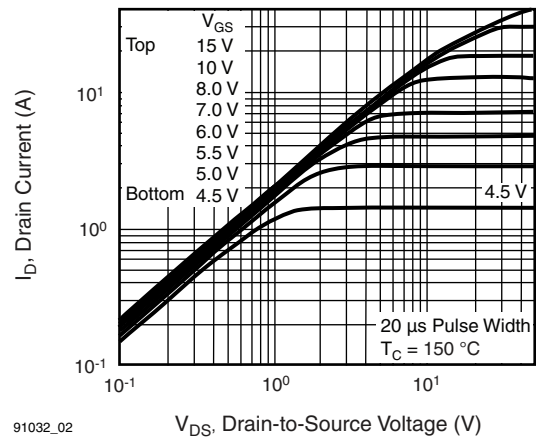


Fig. 2 - Typical Output Characteristics, T<sub>C</sub> = 150 °C

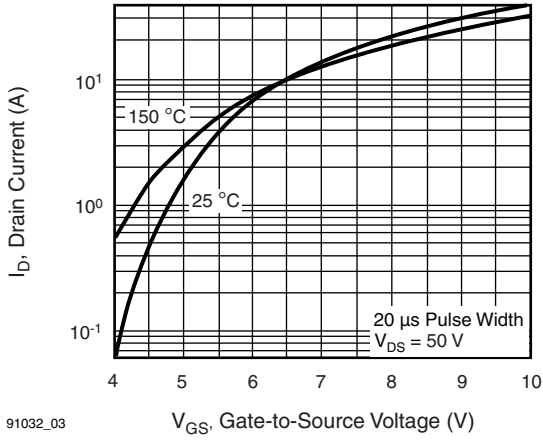


Fig. 3 - Typical Transfer Characteristics

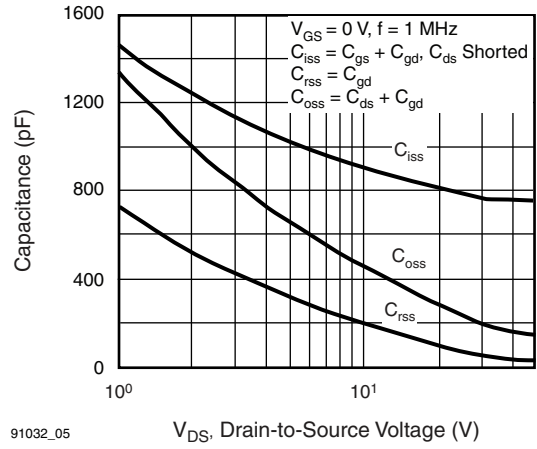


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

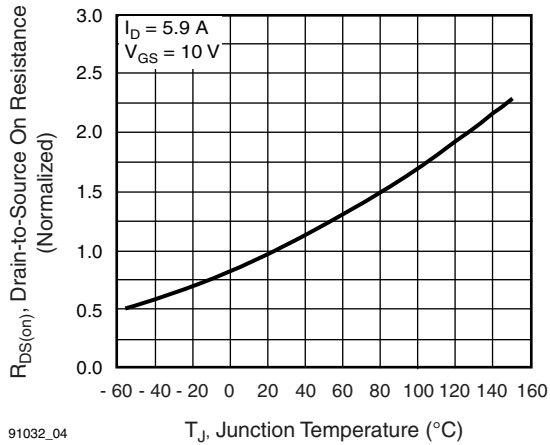


Fig. 4 - Normalized On-Resistance vs. Temperature

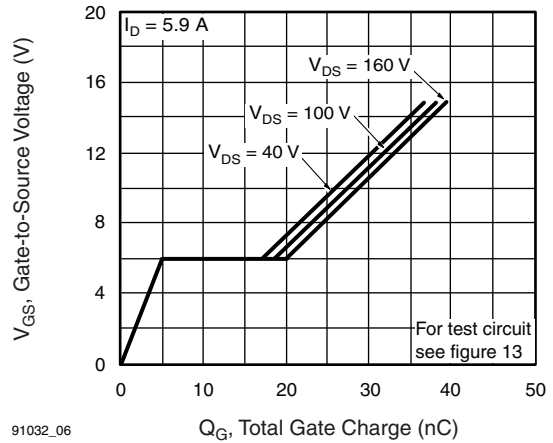
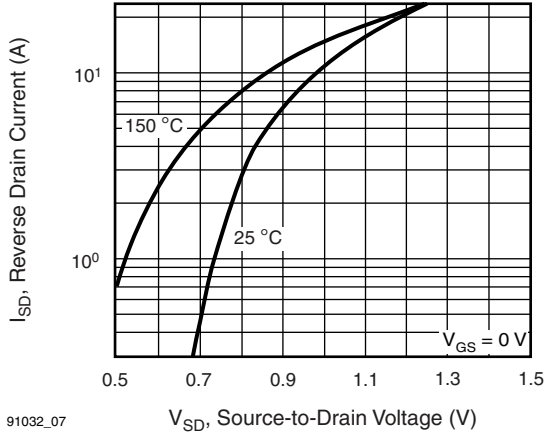
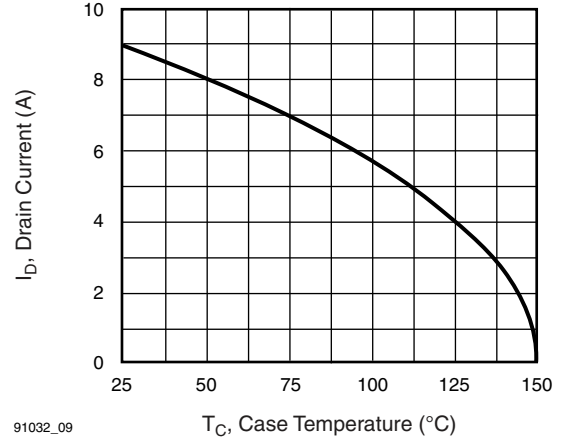


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



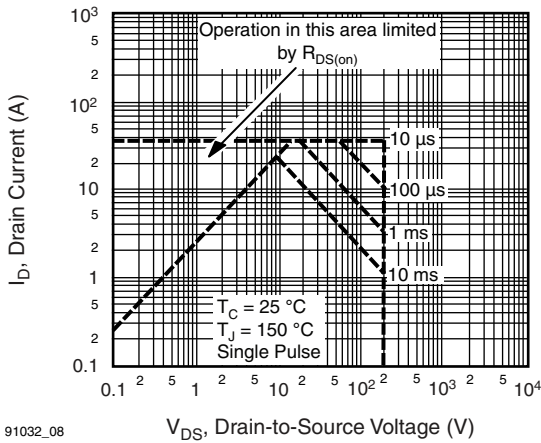
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



91032\_09

Fig. 9 - Maximum Drain Current vs. Case Temperature



91032\_08

Fig. 8 - Maximum Safe Operating Area

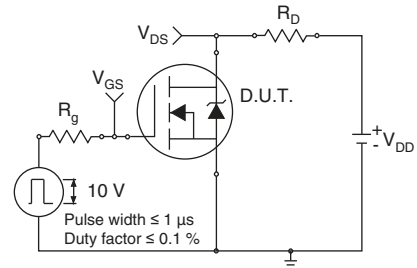


Fig. 10a - Switching Time Test Circuit

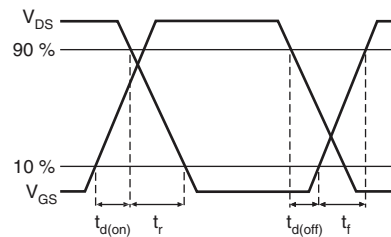


Fig. 10b - Switching Time Waveforms

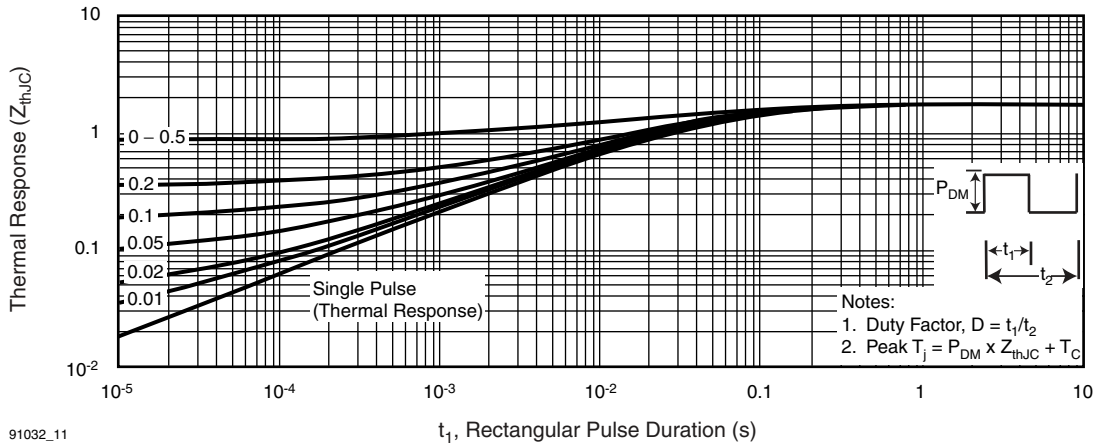


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

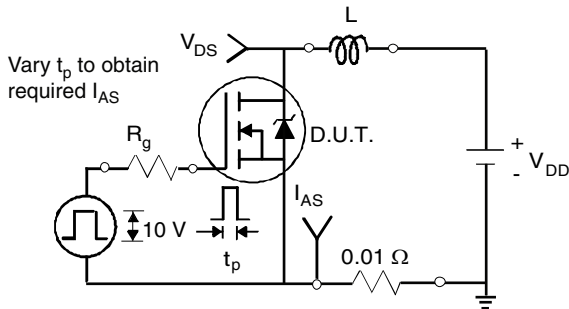


Fig. 12a - Unclamped Inductive Test Circuit

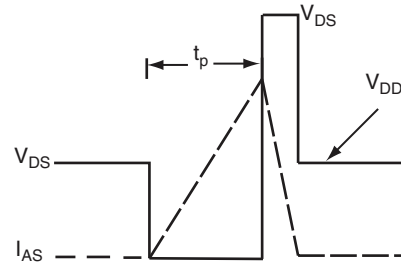


Fig. 12b - Unclamped Inductive Waveforms

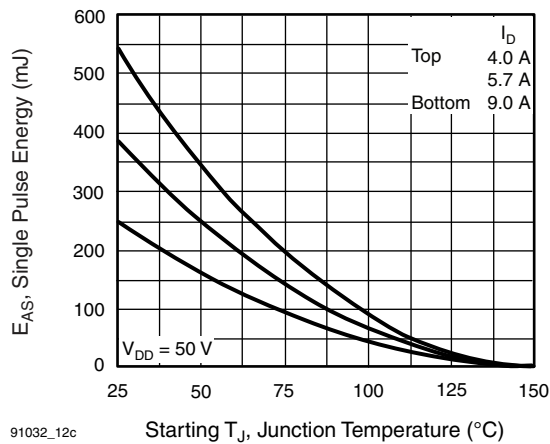


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

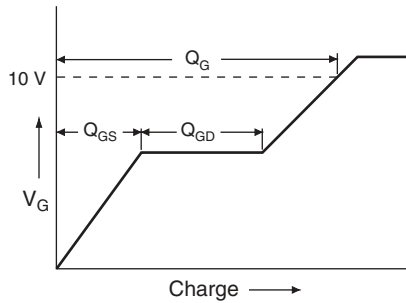


Fig. 13a - Basic Gate Charge Waveform

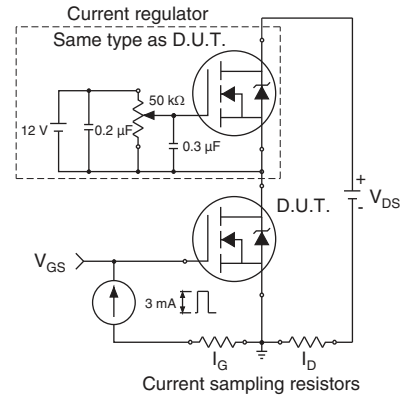
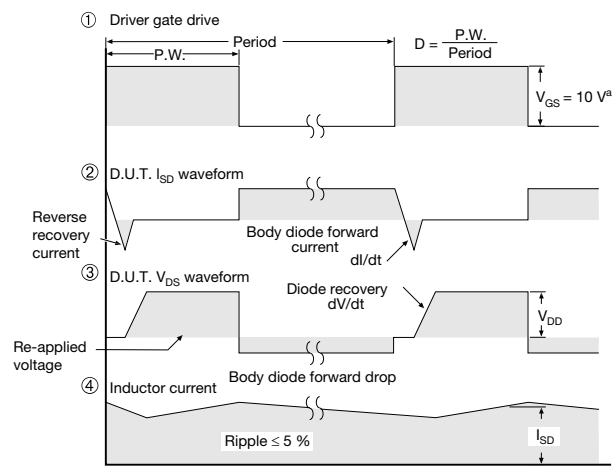
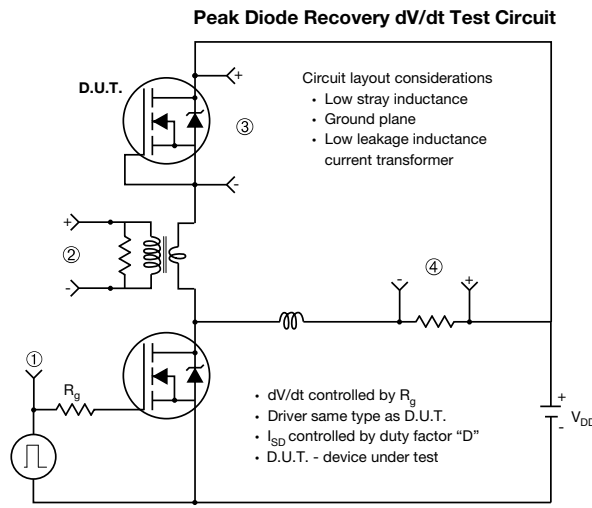


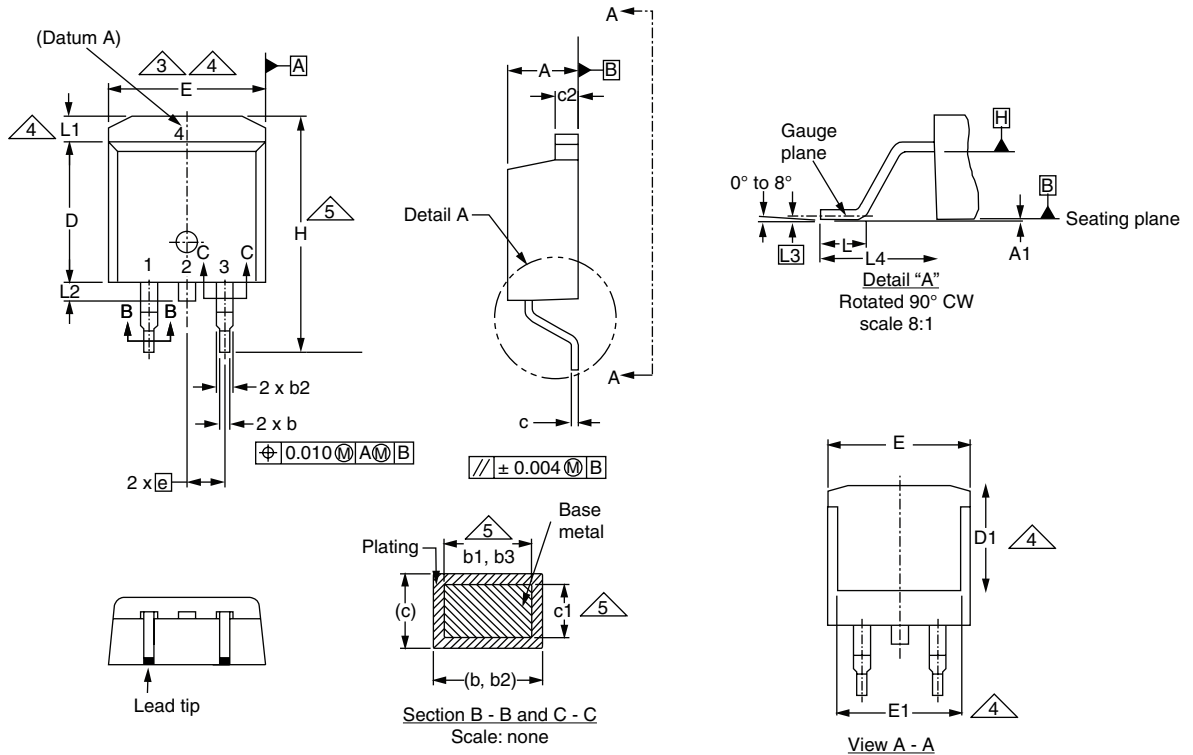
Fig. 13b - Gate Charge Test Circuit



**Note**  
a.  $V_{GS} = 5\text{ V}$  for logic level devices

Fig. 14 - For N-Channel

**TO-263AB (HIGH VOLTAGE)**



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08  
DWG: 5970

**Notes**

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.



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